

Choong Hee Lee

List of Publications by Year in descending order

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13
papers

1,172
citations

933447

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1281871

11
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13
docs citations

13
times ranked

2604
citing authors

#	ARTICLE	IF	CITATIONS
1	Room Temperature Intrinsic Ferromagnetism in Epitaxial Manganese Selenide Films in the Monolayer Limit. Nano Letters, 2018, 18, 3125-3131.	9.1	567
2	p-type doping of MoS ₂ thin films using Nb. Applied Physics Letters, 2014, 104, 092104.	3.3	268
3	Layer-transferred MoS ₂ /GaN PN diodes. Applied Physics Letters, 2015, 107, .	3.3	69
4	High current density 2D/3D MoS ₂ /GaN Esaki tunnel diodes. Applied Physics Letters, 2016, 109, .	3.3	65
5	Epitaxial growth of large area single-crystalline few-layer MoS ₂ with high space charge mobility of $192 \text{ \AA}^2 \text{ V}^{-1} \text{ s}^{-1}$. Applied Physics Letters, 2014, 105, .	3.3	57
6	Molecular beam epitaxy of 2D-layered gallium selenide on GaN substrates. Journal of Applied Physics, 2017, 121, .	2.5	52
7	Growth and electrical characterization of two-dimensional layered MoS ₂ /SiC heterojunctions. Applied Physics Letters, 2014, 105, .	3.3	42
8	Transferred large area single crystal MoS ₂ field effect transistors. Applied Physics Letters, 2015, 107, .	3.3	21
9	BaTiO ₃ /Al _{0.58} Ga _{0.42} N lateral heterojunction diodes with breakdown field exceeding 8 MV/cm. Applied Physics Letters, 2020, 116, .	3.3	17
10	Large-area SnSe ₂ /GaN heterojunction diodes grown by molecular beam epitaxy. Applied Physics Letters, 2017, 111, .	3.3	11
11	Molecular beam epitaxy of GaN on 2H-MoS ₂ . Applied Physics Letters, 2020, 117, .	3.3	3
12	Exploring Thermal Properties of MoS ₂ Using In Situ Quantitative STEM. Microscopy and Microanalysis, 2016, 22, 912-913.	0.4	0
13	Atomic Scale Structure and Defects in 2D GaSe Films and Van der Waals Interface. Microscopy and Microanalysis, 2017, 23, 1728-1729.	0.4	0